

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

**Listing of Claims:**

Claim 1 (original): A silicon carbide epitaxial wafer which is formed on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an  $\alpha$ -type crystal structure.

Claim 2 (currently amended): The silicon carbide epitaxial wafer according to claim 1, wherein said silicon carbide epitaxial wafer is formed on a ~~substrate of the~~ {0001} C face of the substrate.

Claims 3-5 (canceled).

Claim 6 (original): A manufacturing method of a silicon carbide epitaxial wafer, wherein silicon carbide is epitaxially grown on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an  $\alpha$ -type crystal structure.

Claim 7 (currently amended): The manufacturing method of a silicon carbide epitaxial wafer according to claim 6, wherein silicon carbide is epitaxially grown on a ~~substrate of the~~ {0001} C face of the substrate.

Claim 8-15 (canceled).

Claim 16 (new): A silicon carbide epitaxial wafer according to claim 2, wherein said substrate is a silicon carbide substrate having a 4H crystal structure.

Claim 17 (new): A silicon carbide epitaxial wafer according to claim 16, wherein said silicon carbide epitaxial wafer has a flat surface.

Claim 18 (new): A silicon carbide epitaxial wafer according to claim 17, further comprising a semiconductor device formed on said silicon carbide epitaxial wafer.

Claim 19 (new): A silicon carbide epitaxial wafer according to claim 1, wherein said substrate is a silicon carbide substrate having a 4H crystal structure.

Claim 20 (new): A silicon carbide epitaxial wafer according to claim 1, wherein said silicon carbide epitaxial wafer has a flat surface.

Claim 21 (new): A silicon carbide epitaxial wafer according to claim 1, further comprising a semiconductor device formed on said silicon carbide epitaxial wafer.

Claim 22 (new): A method according to claim 6, wherein said silicon carbide is epitaxially grown on a silicon carbide substrate having a 4H crystal structure.

Claim 23 (new): A method according to claim 6, further comprising the step of cleansing a surface of said substrate with a mixed gas of hydrogen gas and propane gas at 1400°C to 1600°C.

Claim 24 (new): A method according to claim 6, wherein said substrate has a surface step with a height of 1nm or less.

Claim 25 (new): A method according to claim 6, wherein, when said silicon carbide is epitaxially grown, a source gas of silane and propane is used.

Claim 26 (new): A method according to claim 25, wherein, when said silicon carbide is epitaxially grown, a growth pressure of 250mbar or less is used.

Claim 27 (new): A method according to claim 26, wherein said source gas has a compositional ratio of C and Si of 1 or less.

Claim 28 (new): A silicon carbide epitaxial wafer prepared by a process comprising the steps of epitaxially growing silicon carbide on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an  $\alpha$ -type crystal structure.

Claim 29 (new): A silicon carbide epitaxial wafer according to claim 28, wherein silicon carbide is epitaxially grown on a {0001} C face.

Claim 30 (new): A silicon carbide epitaxial wafer according to claim 29, wherein said silicon carbide is epitaxially grown on a silicon carbide substrate having a 4H crystal structure.

Claim 31 (new): A silicon carbide epitaxial wafer according to claim 28, wherein a semiconductor device is formed on said silicon carbide epitaxial wafer.